

ABSTRACT

Applicant presents replacement Abstract below indicating the changes with insertions indicated by underlining and deletions indicated by strikeouts and/or double bracketing.

-- The invention relates to a TFA image sensor with stability-optimized photodiode for converting electromagnetic radiation into an intensity-dependent photocurrent with an intermetal dielectric, on which, in the region of the pixel matrix, a lower barrier layer (~~metal-2~~) is situated and a conductive layer (~~metal-2~~) is situated on said the barrier layer, and vias being provided for the contact connection to the ASIC, said the vias in metal contacts on the ASIC. [[¶]] ~~The invention is based on the object of providing a~~ A TFA image sensor having improved electrical properties is provided. This is achieved in that an intrinsic absorption layer (+) is provided between the TCO layer and the barrier layer (~~metal-2~~) with a layer thickness of between 300 nm and 600 nm. Before the application of the photodiodes, the topmost, comparatively thick metal layer of the ASIC is removed and replaced by a matrix of thin metal electrodes which form the back electrodes of the photodiodes, said the matrix being patterned in the pixel raster. (Figure 11)--